

PCN Number:	20171128000	PCN Date:	Dec 5, 2017
Title:	AFE5816ZAV/AFE58JD16ZAV Design Change and Datasheet Updates		
Customer Contact:	PCN Manager	Dept:	Quality Services
Proposed 1st Ship Date:	Mar 5, 2018	Estimated Sample Availability:	Date provided at sample request.
Change Type:			
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process
<input checked="" type="checkbox"/>	Design	<input checked="" type="checkbox"/>	Electrical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material
<input type="checkbox"/>	Wafer Fab Site	<input type="checkbox"/>	Wafer Fab Materials
		<input type="checkbox"/>	Part number change

PCN Details

Description of Change:

This notification is to inform of a design change to the AFE5816ZAV and AFE58JD16ZAV devices. Affected devices are listed in the Product Affected section of this document.

The design change is to suppress VCA and memory write glitches for improving overall performance.

The datasheet numbers will be changing:

	Current	New
Device	Datasheet Number	Datasheet Number
AFE5816ZAV	SBAS688D	SBAS688E
AFE58JD16ZAV	SBAS719	SBAS719A

The product datasheet(s) is also updated as seen in the change revision history below:

AFE5816 16-Channel Ultrasound AFE With 90-mW/Channel Power, 1-nV/ $\sqrt{\text{Hz}}$ Noise, 14-Bit, 65-MSPS or 12-Bit, 80-MSPS ADC and Passive CW Mixer

Changes from Revision D (November 2015) to Revision E	Page
• Deleted <i>Output and Gain Code Step Response vs Time</i> figure.....	24
• Deleted condition statement from <i>Output and Gain Code Step Response vs Time</i> figure.....	24
• Changed <i>Device Power vs Gain Code</i> figure.....	25
• Deleted <i>Device Power vs Gain Code (TGC_CONS register bit = 1)</i> figure	25
• Changed <i>VCA Power vs Gain Code</i> figure	25
• Changed <i>AVDD_1P9 Supply Current vs Gain Code</i> figure.....	26
• Deleted contour curves from <i>Typical Characteristics: TGC Mode</i> section.....	26
• Changed <i>Input Signal Support in TGC Mode</i> section	32
• Added footnote 2 to <i>Profile Description for Up, Down Ramp Mode</i> table	39
• Changed TGC_SLOPE and TGC_UP_DN clock traces in <i>External Non-Uniform Mode</i> figure.....	40
• Added footnote 2 to <i>Profile Description for External Non-Uniform Mode</i> table	41
• Changed Figure 72	45
• Added footnote 2 to <i>Internal Non-Uniform Mode Profile Definition</i> table	47
• Added <i>Latency Between a Transition in TGC_SLOPE and the Resulting Change in Gain</i> table and associated paragraph to <i>Timing Specifications</i> section.....	47
• Changed second sentence in sixth paragraph of <i>Continuous-Wave (CW) Beamformer</i> section	51
• Changed Figure 77	52
• Changed last paragraph of $16 \times f_{cw}$ <i>Mode</i> section	53
• Changed <i>Clock Configurations</i> figure	56
• Changed Number of samples from "2045" to "2047" in Table 15	67
• Changed <i>HPF_ROUND_ENABLE</i> register bit (register 21, bit 5) to <i>HPF_ROUND_EN_CH1-8</i> and	
 Revision History (continued)	
• <i>HPF_ROUND_EN_CH9-16</i> bits in last paragraph of <i>Digital HPF</i> section	69
• Added last paragraph to <i>Partial Power-Up and Power-Down Mode</i> section	76
• Added PLL initialization method (step 4) to <i>Initialization Set Up</i> section	84
• Added <i>PLL Initialization</i> section.....	86
• Changed <i>PIN_PAT_LVDS</i> to <i>PAT_LVDS15[2:0]</i> in register 59 of <i>ADC Register Map</i> table	97
• Added registers 65 and 66 to <i>ADC Register Map</i> table.....	97
• Changed 001 row description from <i>half frame 0, half frame 1</i> to <i>half frame 1, half frame 0</i> in <i>Pattern Mode Bit Description</i> table	99
• Changed <i>HPF_ROUND_EN</i> to <i>HPF_ROUND_EN_CH1-8</i> in register 21	108
• Changed bit 5 from 0 to <i>HPF_ROUND_EN_CH9-16</i> in register 45	122
• Changed bits 7-5 from <i>PIN_PAT_LVDS</i> to <i>PAT_LVDS15[2:0]</i> in register 59	130
• Added register descriptions for registers 65 and 66	132
• Deleted register 202 from <i>VCA Register Map</i> table	134
• Deleted WEBENCH from <i>Related Documentation</i> section	158



AFE58JD16 16-Channel Ultrasound AFE with 90-mW/Channel Power, 1-nV/ $\sqrt{\text{Hz}}$ Noise, 14-Bit, 65-MSPS or 12-Bit, 80-MSPS ADC and Passive CW Mixer

Changes from Original (August 2015) to Revision A	Page
• Deleted <i>Output and Gain Code Step Response vs Time</i> figure	26
• Deleted condition from <i>Output and Gain Code Step Response vs Time</i> figure	26
• Changed <i>Device Power vs Gain Code</i> figure	27
• Deleted <i>Device Power vs Gain Code (TGC_CONS Register Bit = 1)</i> figure	27
• Changed <i>VCA Power vs Gain Code</i> figure	27
• Changed <i>AVDD_1P9 Supply Current vs Gain Code</i> figure	28
• Changed <i>Total Power Dissipation vs ADC Sample Rate</i> figure	28
• Deleted contour figures from <i>Typical Characteristics: TGC Mode</i> section	28
• Changed <i>Input to the device</i> conditions of <i>Typical Characteristics: Demodulator</i> section	30
• Changed <i>Input Signal Support in TGC Mode</i> section	37
• Added note 2 to <i>Profile Description for Up, Down Ramp Mode</i> table	44
• Changed TGC_SLOPE and TGC_UP_DN clock traces in <i>External Non-Uniform Mode</i> figure	45
• Added note 2 to <i>Profile Description for External Non-Uniform Mode</i> table	46
• Changed <i>Internal Non-Uniform Mode Operation</i> figure	50
• Added note 2 to <i>Internal Non-Uniform Mode Profile Definition</i> table	52
• Added <i>Latency Between a Transition in TGC_SLOPE and the Resulting Change in Gain</i> table and associated paragraph to <i>Timing Specifications</i> section	52
• Changed <i>However to Though not shown in Equation 5</i> , in <i>Continuous-Wave (CW) Beamformer</i> section	56
• Changed Figure 87	57
• Changed last paragraph of $16 \times f_{cw}$ <i>Mode</i> section	58
• Changed <i>Clock Configurations</i> figure	61

Revision History (continued)

• Changed number of samples from 2045 to 2047 in <i>Auto Offset Removal Accumulator Cycles</i> table	67
• Changed <i>HPF_ROUND_ENABLE register bit (register 21, bit 5) to HPF_ROUND_EN_CH1-8 and HPF_ROUND_EN_CH9-16 bits</i> in <i>Digital HPF</i> section	69
• Changed <i>Demodulator</i> section	69
• Changed <i>Masking of the Various Reset Operations Resulting from SYNC~ or SYSREF</i> table	97
• Added <i>Interfacing SYNC~ and SYSREF Between the FPGA and AFEs</i> section	103
• Changed <i>Circuit to Level-Shift the Common-Mode Voltage From 1.2 V at the Driver Output to 0.7 V at the AFE Input</i> figure	103
• Changed <i>AC-Coupling Scheme for SYSREF</i> figure	104
• Added <i>AFE58JD16 Family Comparison</i> section, moved location of table to <i>Feature Description</i> section	110
• Added last paragraph to <i>Partial Power-Up and Power-Down Mode</i> section	113
• Changed last paragraph of <i>Register Readout</i> section	116
• Added PLL initialization method to <i>Initialization Set Up</i> section	121
• Added <i>PLL Initialization</i> section	123
• Changed bits 6 and 7 from 0 to COMP_FACTOR_JESD in register 3 of <i>ADC Register Map</i> table	135
• Added <i>_CH1-8</i> to bit 5 in register 21 of <i>ADC Register Map</i> table	135
• Changed bit 5 from 0 to HPF_ROUND_EN_CH9-16 in register 45 of <i>ADC Register Map</i> table	136
• Changed PIN_PAT_LVDS15[2:0] to PAT_LVDS in register 59 in <i>ADC Register Map</i> table	136
• Added register 65 and register 66 to <i>ADC Register Map</i> table	136

- Changed *half frame 0, half frame 1* to *half frame 1, half frame 0* in description of row 001 in *Pattern Mode Bit Description* table 138
- Changed bits 7, 6, and 4 in register 3 139
- Changed bits 14 to 9 in register 4 140
- Changed bit 5 in register 21 147
- Added footnote to bit 0 of *Register 33 Field Descriptions* table 154
- Changed bit 5 in register 45 161
- Added footnote to bit 0 row of *Register 57 Field Descriptions* table 168
- Changed bits 7 to 5 in register 59 169
- Added Register descriptions for registers 65 and 66 171
- Deleted register 202 from *VCA Register Map* section..... 173
- Changed description for JESD_RESET1 in Register 70..... 198
- Changed description of JESD_RESET2 and JESD_RESET3 in Register 74..... 200
- Changed bit 7 from MANUAL_FSWEEEP_EN to FSWEEEP_EN in register 144 of *DEMODO Register Map* table 212
- Changed bits 15 to 11 from 0 to PROFILE_INDEX in register 158 of *DEMODO Register Map* table 212
- Added footnote to *DEMODO Register Map* table 212
- Changed bit 7 of register 144 213
- Changed bit code of bits 7 to 0 from R/W to W in register 150..... 216
- Changed bit code of bits 7 to 0 from R/W to W in register 151..... 216
- Changed bit code of bits 15 to 5 from R/W to W in register 152..... 217
- Changed bit code of bits 15 to 0 from R/W to W in register 153..... 217
- Changed SYNC_WORD default value in register 155 218
- Changed TM_SINE_AMP and TM_SINE_STEP default values in register 159 220
- Deleted WEBENCH from *Related Documentation* section 221

Reason for Change:

Suppress VCA and memory write glitches

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

Die Rev designator will change as shown in the table and sample label below:

Current	New
Die Rev [2P]	Die Rev [2P]
A	B

Sample product shipping label (not actual product label)

 <p>TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 2Q:</p> <table border="1" style="font-size: small;"> <tr> <td>MSL 2 /260C/1 YEAR</td> <td>SEAL DT</td> </tr> <tr> <td>MSL 1 /235C/UNLIM</td> <td>03/29/04</td> </tr> </table> <p>OPT: ITEM: 39 LBL: 5A (L)T0:1750</p>	MSL 2 /260C/1 YEAR	SEAL DT	MSL 1 /235C/UNLIM	03/29/04	 	<p>(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483SI2 (P) (2P) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS</p>
MSL 2 /260C/1 YEAR	SEAL DT					
MSL 1 /235C/UNLIM	03/29/04					

Product Affected: Design Change and datasheet updates

AFE5816ZAV	AFE58JD16ZAV
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Qualification Report

Die-Rev for VCA glitch enhancement - MCM, AFE5816ZAV (RFAB+DMOS6+TITL)
Approve Date 16-Nov-2017

Product Attributes

Attributes	Qual Device: <u>AFE5816ZA</u> <u>V</u>	QBS Product Reference: <u>AFE5816ZA</u> <u>V (PG1.1)</u>	QBS Product Reference: <u>AFE5818ZB</u> <u>V (PG1.0)</u>	QBS Process Reference: <u>SN75DP130DSRGZ</u> <u>R</u>	QBS Process Reference: <u>VSP6825BZR</u> <u>C</u>	QBS Package Reference: <u>AFE5808ZC</u> <u>E</u>	QBS Package Reference: <u>HPAWAVE3ZC</u> <u>E</u>	QBS Package Reference: <u>SN0711033ZC</u> <u>L</u>
Assembly Site	AP3	AP3	AMK-K4	CLARK	PHI	AP3	AP3	AP3
Package Family	NFBGA	NFBGA	NFBGA	QFN	JRBGA	NFBGA	NFBGA	NFBGA
Flammability Rating	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0	UL 94 V-0
Wafer Fab Supplier	DMOS6, RFAB	DMOS6, RFAB	DMOS6, FFAB	DMOS6	HIJI, RFAB	DMOS5, FFAB	DM6	DM5
Wafer Process	C05.2, C027.A	C027.A, C05.2	C027.A, BICOM3X	C027.A	C05, LBC4	C05, BICOM3X	C027.0	A035.1

- QBS: Qual By Similarity
- Qual Device AFE5816ZAV is qualified at LEVEL3-260C
- Device AFE5816ZAV contains multiple dies.

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: <u>AFE5816Z</u> <u>AV</u>	QBS Product Reference: <u>AFE5816Z</u> <u>AV (PG1.1)</u>	QBS Product Reference: <u>AFE5818Z</u> <u>BV (PG1.0)</u>	QBS Process Reference: <u>SN75DP130DSR</u> <u>GZR</u>	QBS Process Reference: <u>VSP6825B</u> <u>ZRC</u>	QBS Package Reference: <u>AFE5808Z</u> <u>CF</u>	QBS Package Reference: <u>HPAWAVE3</u> <u>ZCF</u>	QBS Package Reference: <u>SN0711033</u> <u>ZCL</u>
AC	Autoclave 121C	96 Hours	-	-	-	3/231/0	-	-	1/77/0	-
ED	Electrical Characterization	Per Datasheet Parameters	Pass	-	-	Pass	-	Pass	Pass	Pass
ELFR	Early Life Failure Rate, 125C	48 Hours	-	-	3/3000/0	3/1852/0	-	-	-	-
HAST	Biased HAST, 130C/85%RH	96 Hours	-	-	3/162/0	3/225/0	3/230/0	-	-	3/231/0
HBM	ESD - HBM	4000 V	1/3/0	-	2/6/0	-	-	-	-	-
CDM	ESD - CDM	1500 V	1/3/0	-	-	-	-	1/3/0	1/3/0	-
HTOL	Life Test, 125C	1000 Hours	-	-	3/231/0	3/231/0	-	-	1/77/0	3/231/0
HTOL	Life Test, 140C	480 Hours	-	-	-	-	3/231/0	-	-	-
HTSL	High Temp. Storage Bake, 150C	1000 Hours	-	-	-	-	-	-	-	3/231/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	-	3/231/0	3/231/0	3/231/0	-	1/77/0	-
LU	Latch-up	(per JESD78)	-	1/6/0	2/12/0	3/18/0	2/12/0	1/6/0	1/6/0	3/18/0
PD	Physical Dimensions	--	-	-	-	-	-	-	-	3/15/0
SBS	Solder Ball Shear	--	-	1/77/0	3/231/0	-	-	-	-	2/154/0
TC	Temperature Cycle, -55/125C	700 Cycles	-	1/77/0	3/231/0	-	-	1/77/0	-	3/231/0

TC	Temperature Cycle, -65/150C	500 Cycles	-	-	-	3/231/0	3/231/0	-	1/77/0	-
UHA ST	Unbiased HAST 110C/85%RH	264 Hours	-	1/77/0	3/231/0	-	-	-	-	-
UHA ST	Unbiased HAST 130C/85%RH	96 Hours	-	-	-	3/231/0	-	-	-	3/231/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com